# ne<mark>x</mark>peria

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Should be replaced with:

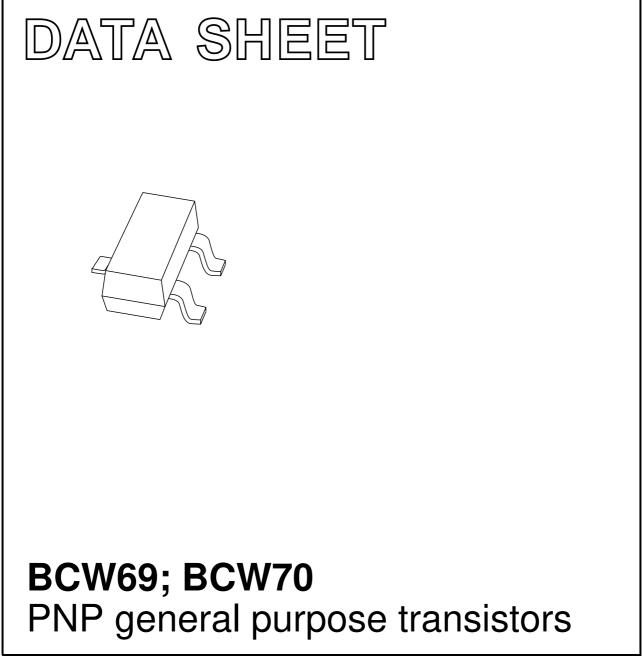
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 19 2004 Feb 06



#### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

#### **APPLICATIONS**

• General purpose switching and amplification.

#### DESCRIPTION

PNP transistor in a SOT23 plastic package. NPN complements: BCW71 and BCW72.

#### MARKING

| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| BCW69       | H1*                         |
| BCW70       | H2*                         |

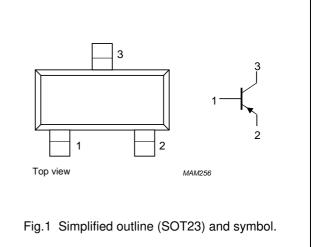
#### Note

- 1. \* = p : Made in Hong Kong.
  - \* = t : Made in Malaysia.

\* = W : Made in China.

#### **ORDERING INFORMATION**

| PIN | DESCRIPTION |  |
|-----|-------------|--|
| 1   | base        |  |
| 2   | emitter     |  |
| 3   | collector   |  |



| TYPE   | PACKAGE |  |         |
|--------|---------|--|---------|
| NUMBER | NAME    | DESCRIPTION                              | VERSION |
| BCW69  | _       | plastic surface mounted package; 3 leads | SOT23   |
| BCW70  |         |  |         |

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter                     | -    | -50  | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base; $I_C = -2 \text{ mA}$ | -    | -45  | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | -    | -5   | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | -    | -100 | mA   |
| I <sub>CM</sub>  | peak collector current        |                                  | -    | -200 | mA   |
| I <sub>BM</sub>  | peak base current             |                                  | -    | -200 | mA   |
| P <sub>tot</sub> | total power dissipation       | $T_{amb} \le 25 \ ^{\circ}C$     | -    | 250  | mW   |
| T <sub>stg</sub> | storage temperature           |                                  | -65  | +150 | °C   |
| Tj               | junction temperature          |                                  | -    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | -65  | +150 | °C   |

## BCW69; BCW70

# BCW69; BCW70

#### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                   | CONDITIONS | VALUE | UNIT |  |
|----------------------|---|------------|-------|------|--|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | note 1     | 500   | K/W  |  |

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

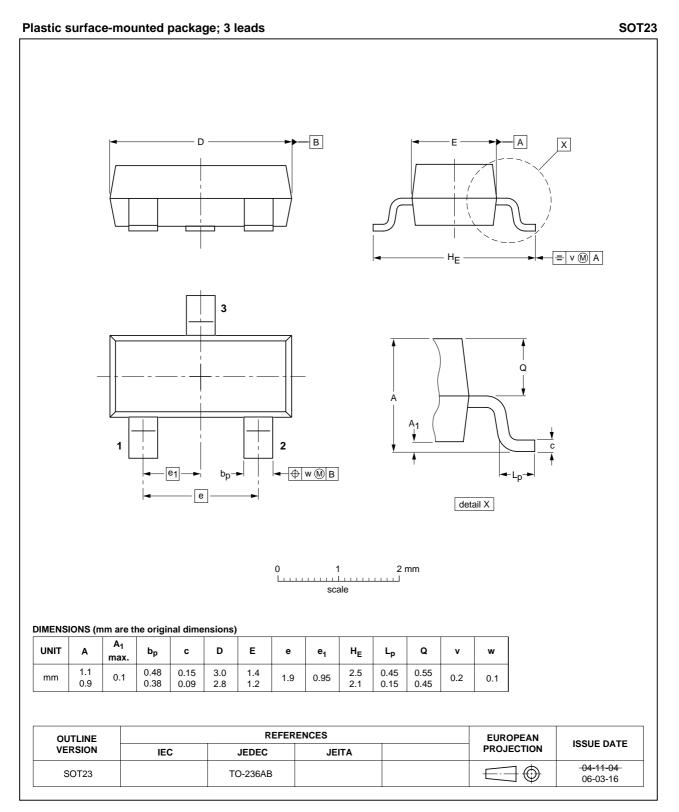
| SYMBOL             | PARAMETER                       | CONDITIONS  | MIN. | TYP. | MAX. | UNIT |
|--------------------|---------------------------------|---|------|------|------|------|
| I <sub>CBO</sub>   | collector cut-off current       | $I_E = 0; V_{CB} = -20 V$   | -    | _    | -100 | nA   |
|                    |                                 | $I_E = 0; V_{CB} = -20 \text{ V}; T_j = 100 \text{ °C}$   | -    | —    | -10  | μA   |
| I <sub>EBO</sub>   | emitter cut-off current         | $I_{C} = 0; V_{EB} = -5 V$  | _    | _    | -100 | nA   |
| h <sub>FE</sub>    | DC current gain                 | $I_{C} = -10 \ \mu A; \ V_{CE} = -5 \ V$  |      |      |      |      |
|                    | BCW69                           |   | -    | 90   | -    |      |
|                    | BCW70                           |   | _    | 150  | _    |      |
|                    | DC current gain                 | $I_{C} = -2 \text{ mA}; V_{CE} = -5 \text{ V}$  |      |      |      |      |
|                    | BCW69                           |   | 120  | _    | 260  |      |
|                    | BCW70                           |   | 215  | _    | 500  |      |
| V <sub>CEsat</sub> | collector-emitter saturation    | $I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$   | _    | -80  | -300 | mV   |
|                    | voltage                         | $I_{C} = -50 \text{ mA}; I_{B} = -2.5 \text{ mA}; \text{ note } 1$  | _    | -150 | _    | mV   |
| V <sub>BEsat</sub> | base-emitter saturation voltage | $I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$   | _    | -720 | _    | mV   |
|                    |                                 | $I_{C} = -50 \text{ mA}; I_{B} = -2.5 \text{ mA}; \text{ note } 1$  | _    | -810 | _    | mV   |
| V <sub>BE</sub>    | base-emitter voltage            | $I_{\rm C} = -2 \text{ mA}; V_{\rm CE} = -5 \text{ V}$  | -600 | _    | -750 | mV   |
| C <sub>c</sub>     | collector capacitance           | $I_E = I_e = 0; V_{CB} = -10 V;$<br>f = 1 MHz   | -    | 4.5  | -    | pF   |
| f <sub>T</sub>     | transition frequency            | $I_{C} = -10 \text{ mA}; V_{CE} = -5 \text{ V};$<br>f = 100 MHz   | 100  | _    | -    | MHz  |
| F                  | noise figure                    | $    I_{C} = -200 \ \mu\text{A}; \ V_{CE} = -5 \ V; \\ R_{S} = 2 \ k\Omega; \ f = 1 \ k\text{Hz}; \ B = 200 \ \text{Hz} $ | -    | _    | 10   | dB   |

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

## BCW69; BCW70

#### PACKAGE OUTLINE



### BCW69; BCW70

#### DATA SHEET STATUS

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

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## NXP Semiconductors

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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